

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

Abstract

There is provided a technique that includes (a) forming a layer containing a first element on a substrate by performing: (a1) supplying an inhibiting gas to the substrate to form an inhibiting group on the substrate, wherein the inhibiting group inhibits adsorption of a first gas containing an atom of the first element to the substrate; (a2) supplying a promoting gas to the substrate after start of (a1) to form a promoting group on the substrate, wherein the promoting group promotes adsorption of the first gas to the substrate; and (a3) supplying the first gas to the substrate after start of (a2).

Fig. 3G